# Silicon Carbide Schottky Diode

# 650 V, 10 A

## **Description**

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 64 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- This Device is Pb-Free and is RoHS Compliant

#### **Applications**

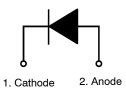
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

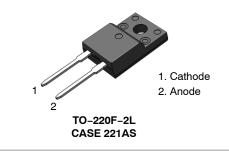


## ON Semiconductor®

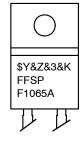
#### www.onsemi.com

V <sub>RRM</sub>	I <sub>F</sub>
650 V	10 A





#### **MARKING DIAGRAM**



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Numeric Date Code &K = Lot Code

FFSPF1065A = Specific Device Code

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, Unless otherwise specified)

Symbol	Parameter		FFSPF1065A	Unit	
$V_{RRM}$	Peak Repetitive Reverse Voltage		650	V	
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		64	mJ	
lF	Continuous Rectified Forward Current @Tc < 110°C		10	Α	
		@ Tc < 135°C	7.2		
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	Tc = 25°C, 10 μs	720	Α	
		Tc = 150°C, 10 μs	680	Α	
I <sub>F, SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>P</sub> = 8.3 ms	56	Α	
I <sub>F, RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>P</sub> = 8.3 ms	28	Α	
P <sub>tot</sub>	Power Dissipation	Tc = 25°C	38	W	
		Tc = 150°C	6.4	W	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	•	-55 to +175	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1.  $E_{AS}$  of 64 mJ is based on starting  $T_J = 25^{\circ}C$ , L = 0.5 mH,  $I_{AS} = 16$  A, V = 50 V.

#### THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{ hetaJC}$	Thermal Resistance, Junction to Case, Max.	3.9	°C/W

#### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSPF1065A	FFSPF1065A	TO-220F-2L	Tube	N/A	N/A	50 Units

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	IF = 10 A, Tc = 25°C	-	1.50	1.75	V
		IF = 10 A, Tc = 125°C	-	1.60	2.0	
		IF = 10 A, Tc = 175°C	-	1.72	2.4	
I <sub>R</sub>	Reverse Current	VR = 650 V, Tc = 25°C	-	-	200	μΑ
		VR = 650 V, Tc = 125°C	-	-	400	
		VR = 650 V, Tc = 175°C	-	-	600	
Q <sub>C</sub>	Total Capacitance Charge	V = 400 V	-	34	-	nC
С	Total Capacitance	VR = 1 V, f = 100 kHz	-	575	-	pF
		VR = 200 V, f = 100 kHz	-	62	-	
		VR = 400 V, f = 100 kHz	-	47	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **TYPICAL CHARACTERISTICS**

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

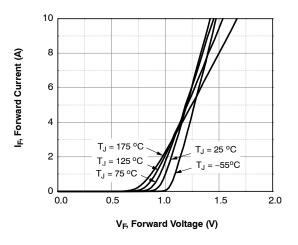


Figure 1. Forward Characteristics

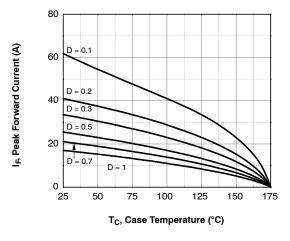


Figure 3. Current Derating

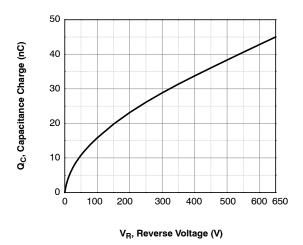


Figure 5. Capacitive Charge vs. Reverse Voltage

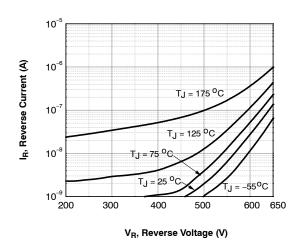


Figure 2. Reverse Characteristics

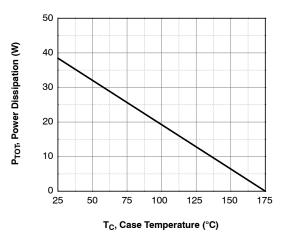


Figure 4. Power Derating

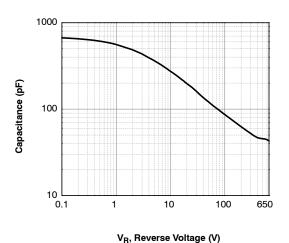
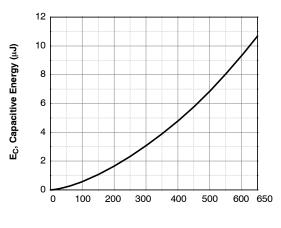


Figure 6. Capacitance vs. Reverse Voltage

## TYPICAL CHARACTERISTICS (Continued)

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 



V<sub>R</sub>, Reverse Voltage (V)

Figure 7. Capacitance Stored Energy

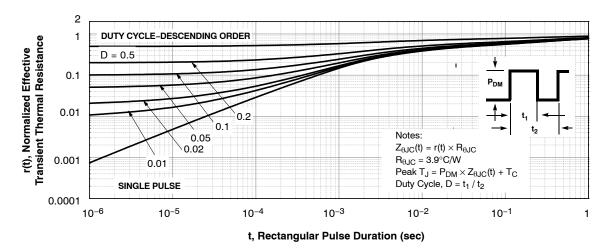
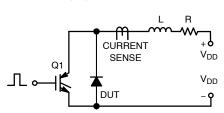


Figure 8. Junction-to-Case Transient Thermal Response Curve

## **TEST CIRCUIT AND WAVEFORMS**

$$\label{eq:local_local_local} \begin{split} L &= 0.5 \text{ mH} \\ R &< 0.1 \ \Omega \\ V_{DD} &= 50 \ V \\ EAVL &= 1/2 Li2 \left[ V_{R(AVL)} / (V_{R(AVL)} - V_{DD}) \right] \\ Q1 &= IGBT \left( BV_{CES} > DUT \ V_{R(AVL)} \right) \end{split}$$



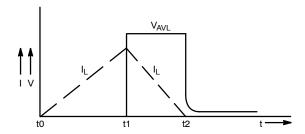
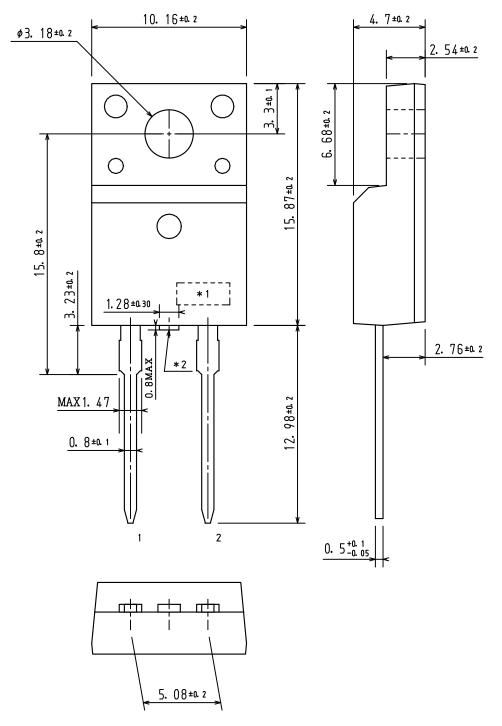


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



#### TO-220 Fullpack, 2-Lead / TO-220F-2FS CASE 221AS ISSUE O

**DATE 29 FEB 2012** 





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